

First Named Inventor	Leonard Forbes
Serial No.	10/808,059
Filing Date	March 24, 2004
Group Art Unit	2814
Examiner Name	M. D. Pizarro Crespo
Confirmation No.	4221
Attorney Docket No.	400.285US01

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INFORMATION DISCLOSURE
STATEMENT
FORM PTO-1449

Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC
FORMED BY THE LOW TEMPERATURE OXIDIZATION OF METALS

#41DS
Sheet 1 of 1

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Examiner Initials	Foreign Patent		Name	Publication Date	Translation
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Examiner Signature	<i>Marcos D. Pizarro</i>	Date Considered	8/3/2005
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			